



### 50V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage 50 V Current 360mA

#### **Features**

- RDS(ON), VGS@10V, ID@500mA<1.45Ω
- RDS(ON), VGS@4.5V, ID@200mA<1.95Ω</li>
- RDS(ON) , VGS@2.5V, ID@100mA<4.0Ω</li>
- RDS(ON), VGS@1.8V, ID@10mA<6.0Ω</li>
- Advanced Trench Process Technology
- ESD Protected 2KV HBM
- Specially Designed for Relay driver, Speed line drive, etc.
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

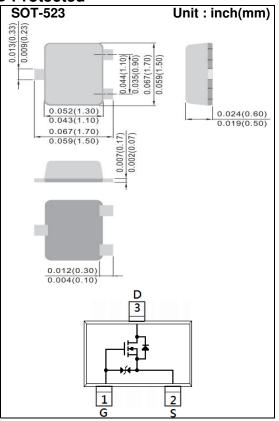
#### **Mechanical Data**

Case: SOT-523 Package

Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.00007 ounces, 0.002 grams

Marking: E38



# Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	50	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	V
Continuous Drain Current		I <sub>D</sub>	360	mA
Pulsed Drain Current		I <sub>DM</sub>	1200	mA
Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	300	mW
	Derate above 25°C		2.4	mW/°C
Operating Junction and Storage Temperature Range		$T_{J}, T_{STG}$	-55~150	°C
Typical Thermal resistance - Junction to Ambient (Note 3)		$R_{ heta JA}$	417	°C/W





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	50	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	0.5	0.86	1.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}=10V,I_{D}=500mA$	-	1.2	1.45	Ω
		V <sub>GS</sub> =4.5V,I <sub>D</sub> =200mA	-	1.3	1.95	
		V <sub>GS</sub> =2.5V,I <sub>D</sub> =100mA	-	1.7	4.0	
		V <sub>GS</sub> =1.8V,I <sub>D</sub> =10mA	-	4.0	6.0	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =50V, $V_{GS}$ =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	<u>+</u> 10	uA
Dynamic (Note 4)						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =25V, I <sub>D</sub> =500mA, V <sub>GS</sub> =4.5V	-	0.95	-	nC
Gate-Source Charge	$Q_gs$		-	0.34	-	
Gate-Drain Charge	$Q_{gd}$		-	0.32	-	
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	36	-	pF
Output Capacitance	Coss		-	11	-	
Reverse Transfer Capacitance	Crss		-	6.6	-	
Turn-On Delay Time	td <sub>(on)</sub>	)/ OF)/   F00 A	-	2.3	-	
Turn-On Rise Time	tr	$\begin{array}{l} V_{DD}{=}25V,\ I_{D}{=}500mA,\\ V_{GS}{=}10V,\\ R_{G}{=}6\Omega \end{array}$	-	20	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	7	-	
Turn-Off Fall Time	tf		-	20	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					500	mA
Diode Forward Current	I <sub>S</sub>		-	-	500	
Diode Forward Voltage	$V_{\text{SD}}$	I <sub>S</sub> =500mA, V <sub>GS</sub> =0V	-	0.9	1.5	V

### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper
- 4. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

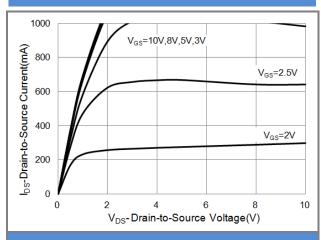
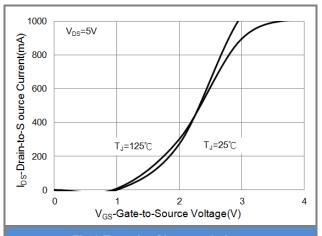


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

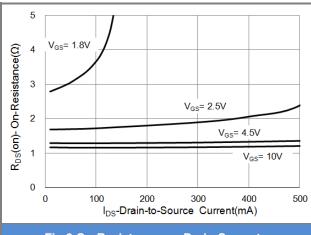


Fig.3 On-Resistance vs. Drain Current

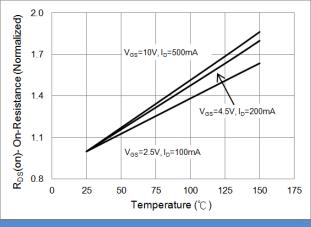
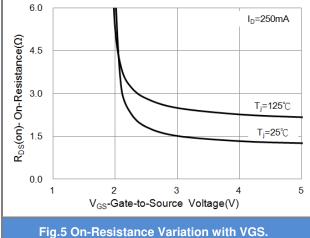
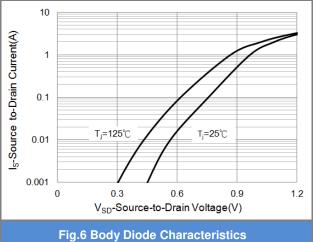


Fig.4 On-Resistance vs. Junction temperature









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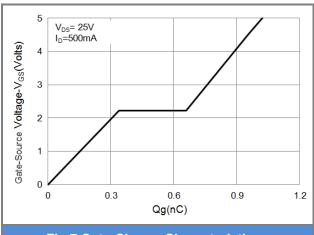


Fig.7 Gate-Charge Characteristics

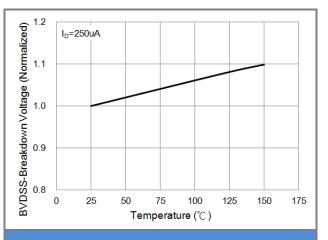


Fig.8 Breakdown Voltage Variation vs. Temperature

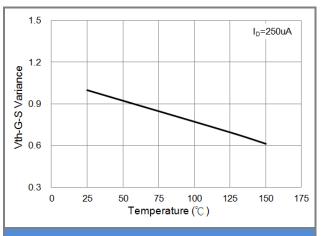


Fig.9 Threshold Voltage Variation with Temperature.

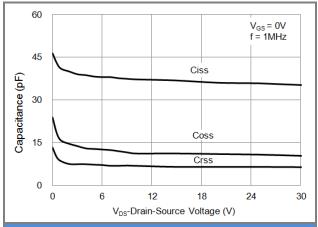


Fig.10 Capacitance vs. Drain-Source Voltage.

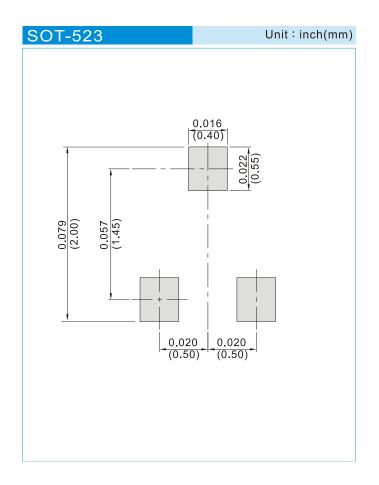




### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJE8438_R1_00001	SOT-523	4K pcs / 7" reel	E38	Halogen free

### **MOUNTING PAD LAYOUT**







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